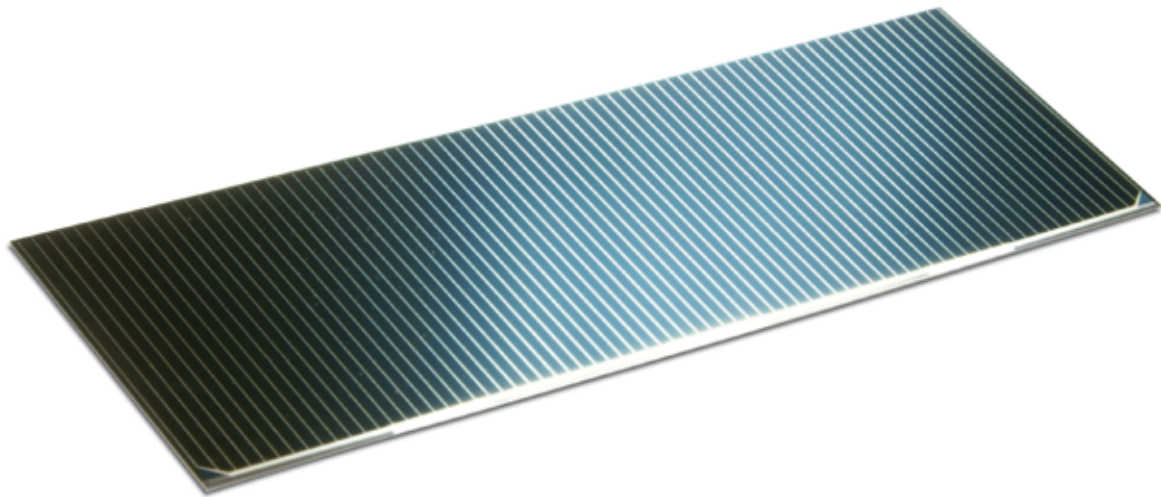
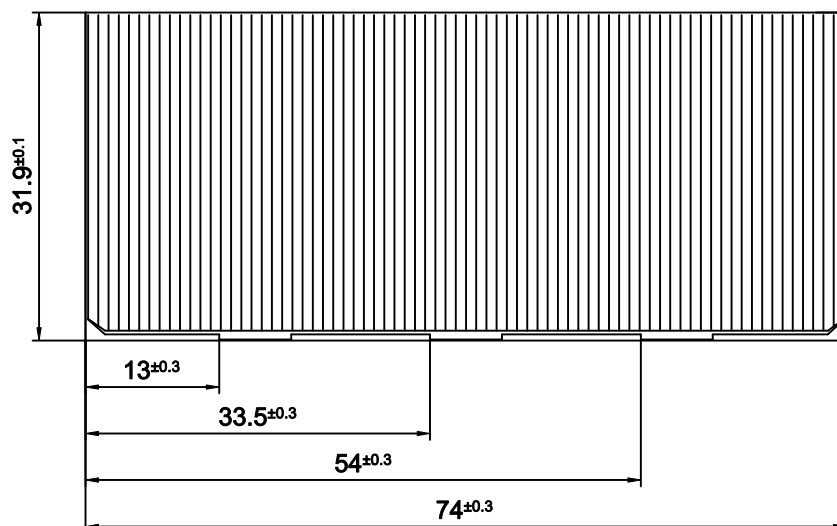


## Cell Type: S 32



This cell type is a state-of-the-art high efficiency, low weight silicon solar cell with an integrated by-pass diode.



# Cell Type: S 32



## Design and Mechanical Data

Base Material	CZ, <1-0-0>
AR-coating	TiO <sub>x</sub> /Al <sub>2</sub> O <sub>3</sub>
Dimensions	74.0 x 31.9 mm ± 0.1 mm
Cell Area	23.61 cm <sup>2</sup>
Average Weight	≤ 32 mg/cm <sup>2</sup>
Cell Thickness	130 ± 30 μm
Ag - Thickness	3 – 11 μm
Grid Design	Improved Grid system with 3 contact pads
Resistivity	ρ (B) 2 ± 1 Ω cm
Shadow Protection	Integrated Zener by-pass diode I <sub>rev</sub> = 55 mA/cm <sup>2</sup> (1.2 Isc) @ V <sub>rev</sub> = 5 – 6 V



## Electrical Data

		BOL	3E14	1E15	3E15
Average Open Circuit V <sub>OC</sub>	[mV]	628	0.91	0.89	0.85
Average Short Circuit I <sub>SC</sub>	[mA/cm <sup>2</sup> ]	45.8	0.88	0.85	0.76
Voltage at max. Power V <sub>pmax</sub>	[mV]	528	0.91	0.89	0.84
Current at max. Power I <sub>pmax</sub>	[mA/cm <sup>2</sup> ]	43.4	0.88	0.84	0.75
Average Efficiency η <sub>bare</sub>	[%]	16.9	0.80	0.74	0.64

Test Conditions: AMO Spectrum; Light Intensity E = 135.3 mW/cm<sup>2</sup>; Cell Temperature T<sub>c</sub> = 28°C

Standard : CNES 01-23MV1

BOL measurement accuracy: ± 1.5% relative



## Temperature Gradients

		- 2.02	-2.14	- 2.17	- 2.20
Voltage dV <sub>oc</sub> /dT	[mV/°C]				
Short Circuit dI <sub>sc</sub> /dT	[mA/cm <sup>2</sup> /C°]	0.030	0.045	0.055	0.059
Voltage dV <sub>pmax</sub> /dT	[mV/°C]	- 2.07	-2.22	- 2.19	- 2.25
Power dP <sub>mpax</sub> /dT	[mW/cm <sup>2</sup> /°C]	0.004	0.023	0.027	0.035



## Threshold Values

Absorptivity	≤ 0.78 (CMX 100 AR/IRR)
Pulltest	> 5 N at 45 ° welding test (with 35 μm Ag stripes)
Development Status	Qualified